

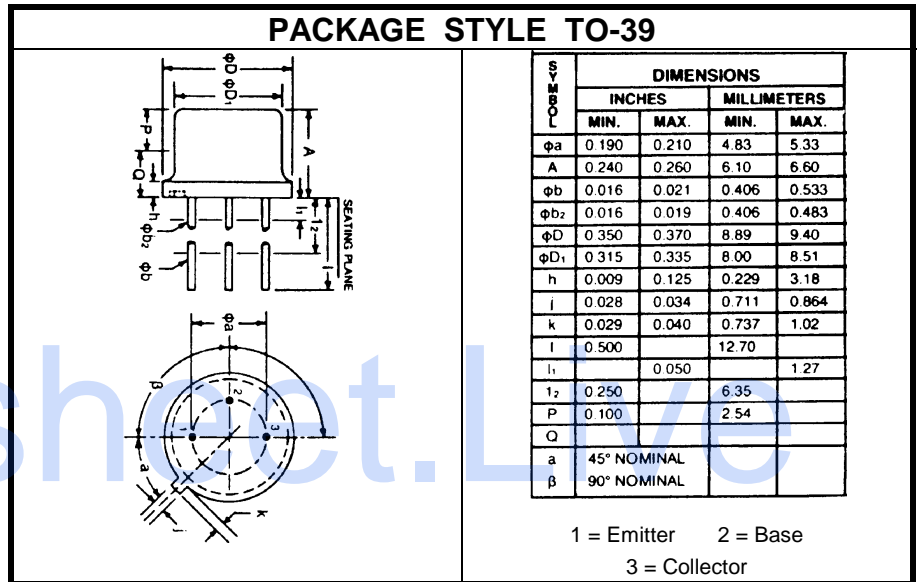
NPN SILICON SWITCHING TRANSISTOR

DESCRIPTION:

The **ASI BFX34** is Designed for General Purpose Medium Power Switching and Amplifier applications.

MAXIMUM RATINGS

I_C	5.0 A
V_{CB0}	120 V
V_{CEO}	60 V
P_{DISS}	5.0 W @ $T_A = 25^\circ\text{C}$
T_J	-65 to +200 °C
T_{STG}	-65 to +200 °C
θ_{JC}	35 °C/W


ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100\text{ mA}$	60			V
BV_{CBO}	$I_C = 5.0\text{ mA}$	120			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	6.0			V
I_{CES}	$V_{CE} = 60\text{ V}$			0.02	μA
I_{EBO}	$V_{EB} = 4.0\text{ V}$			10	μA
h_{FE}	$V_{CE} = 2.0\text{ V}$ $I_C = 1.0\text{ A}$		100		---
	$V_{CE} = 0.6\text{ V}$ $I_C = 2.0\text{ A}$		75		
	$V_{CE} = 2.0\text{ V}$ $I_C = 2.0\text{ A}$	40	80	150	
$V_{CE(SAT)}$	$I_C = 5.0\text{ A}$ $I_B = 500\text{ mA}$			1.0	V
$V_{BE(SAT)}$	$I_C = 5.0\text{ A}$ $I_B = 500\text{ mA}$			1.6	V

DYNAMIC ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
f_t	$V_{CE} = 5.0\text{ V}$ $I_C = 500\text{ mA}$ $f = 20\text{ MHz}$	70			MHz
C_{EBO}	$V_{EB} = 0.5\text{ V}$ $f = 1.0\text{ MHz}$			500	pF
C_{CBO}	$V_{CB} = 10\text{ V}$ $f = 1.0\text{ MHz}$			100	pF
t_{on} t_{off}	$V_{CC} = 20\text{ V}$ $I_C = 0.5\text{ A}$ $I_{B1} = -I_{B2} = 500\text{ mA}$			0.25 1.2	μS